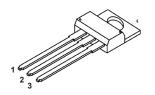
Bipolar Transistor

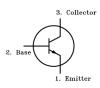


RoHS

Compliant







Description:

A Silicon NPN transistor in a TO-220 type package designed for high-voltage, high-speed power switching inductive circuits where fall time is critical. This device is particularly suited for 115V and 220V switch-mode applications such as switching regulators, inverters, motor controls, solenoid/relay drivers and deflection circuits

Maximum Ratings:

Characteristic	Symbol	Rating	Unit	
Collector-Emitter Voltage	V _{CEO(sus)}	350	V	
Collector-Base Voltage	V _{CBO}	6	v	
Collector Current - Continuous - Peak	Ι _c	5 10	•	
Base Current - Continuous - Peak	Ι _Β	2 12	A	
Total Power Dissipation (T _C = +25°C), Derate Above 25°C	P _D	80 640	W mW/°C	
Operating Junction Temperature	Τ _J	-65 to +150	°C	
Storage Temperature Range	T _{stg}	-65 (0 + 150	C	
Thermal Resistance, Junction-to-case	R _{thjc}	1.56	°C/W	
Lead Temperature (During Soldering, 1/8" from case, 5 sec)	TL	+275	°C	

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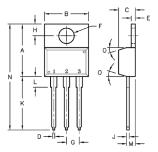
Bipolar Transistor



Parameter	Symbol	Test Conditions	Min.	Тур	Max.	Unit
OFF Characteristics (Note 1)	· · · · · ·				· · · · ·	
Collector - Emitter Sustaining Voltage	V _{CEO(sus)}	I _C = 25mA, I _B = 0	350	-	-	V
Collector Cutoff Current		V _{CEV} = 450V, V _{BE(off)} = 1.5V	-	-	1	mA
	CEV	V_{CEV} = 225V, $V_{BE(off)}$ = 1.5V T _C = 100°	-	-	10	mA
Emitter Cutoff Current	I _{EBO}	$V_{EB} = 6V, I_{C} = 0$	-	-	1	mA
ON Characteristics (Note 1)						
DC Current Gain	h _{FE} -	V _{CE} - 10V, I _C = 2.5A	10	-	75	
		V _{CE} - 10V, I _C = 5A	3	-	-	
Collector - Emitter Saturation Voltage	V	I _C = 2.5A, I _B = .5A	-	-	1.5	V
Conector - Emitter Saturation voltage	V _{CE(sat)}	I _C = 5A, I _B = 2A	-	-	5	V
Pasa Emittar Saturation Voltage	V	I _C = 2.5A, I _B = 0.5A	-	-	1.5	V
Base - Emitter Saturation Voltage	V _{BE(sat)}	I _C = 5A, I _B = 2A	-	-	2.5	V
Dynamic Characteristics						
	1			<u> </u>	<u> </u>	

Switching Characteristics (Resistive Load)									
Output Capacitance	C _{ob}	V _{CB} - 10V, I _E = 0, f = 0.1MHz	-	150	-	pF			
Current Gain - Bandwidth Product	f _T	V _{CE} - 10V, I _C = 250mA, f = 1MHz	5	-	-	MHz			

Note 1 : Pulse test : -Pulse width = 5ms, duty cycle </= 10%



Pin Configuration:

- 1. Emitter
- 2. Base
- 3. Collector

Dim.	Α	В	С	D	E	F	G	н	J	к	L	М	N	0
Min.	14.42	9.63	3.56	-	1.15	3.75	2.29	2.54	-	12.7	2.8	2.03	-	70
Max.	16.51	10.67	4.83	0.9	1.4	3.88	2.79	3.43	0.56	14.73	4.07	2.92	31.24	'

Dimensions : Millimetres

Part Number Table

Description	Part Number			
Transistor, NPN, 5A, 350V, TO-220	2N6499			

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